

Applic. No.: 10/653,794
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Amendments to the Specification:

Please replace the paragraph on page 15, lines 14-19, with the following paragraph:

In principle, an antioxidation layer 1 can also be arranged above a current aperture layer 10. The layers and etch edges that lie exposed after the etching can be protected against oxidation in subsequent processing steps by using a suitable coverlayer 20 (see Fig. 2). A preferred material for the coverlayer is CVD-SiN_x.